

Dual P-Channel NexFET™ Power MOSFET

Check for Samples: [CSD75211W1723](#)

FEATURES

- Dual P-Ch MOSFETs
- Common Source Configuration
- Small Footprint 1.7 mm × 2.3 mm
- Ultra Low Q_g and Q_{gd}
- Pb Free
- RoHS Compliant
- Halogen Free

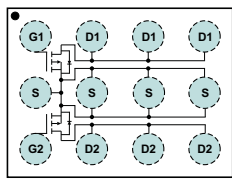
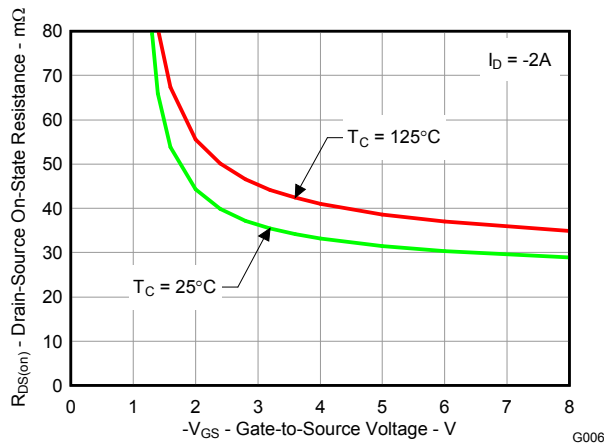
APPLICATIONS

- Battery Management
- Battery Protection
- DC-DC Converters

DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with thermal characteristics in an ultra low profile. Low on resistance and gate charge coupled with the small footprint and low profile make the device ideal for battery operated space constrained application in load management as well as DC-DC converter applications

Top View


 $R_{DS(on)}$ VS V_{GS}


PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	-20	V
Q_g	Gate Charge Total (-4.5V)	4.5	nC
Q_{gd}	Gate Charge Gate to Drain	0.9	nC
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = -1.8V$	50 mΩ
		$V_{GS} = -2.5V$	39 mΩ
		$V_{GS} = -4.5V$	32 mΩ
$V_{GS(th)}$	Threshold Voltage	-0.7	V

ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD75211W1723	1.7-mm × 2.3-mm Wafer Level Package	7-Inch Reel	3000	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

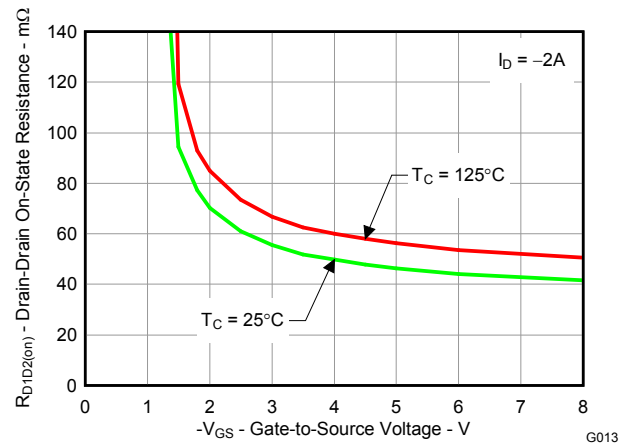
$T_A = 25^\circ\text{C}$ unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	±8	V
I_D	Continuous Drain Current ⁽¹⁾ ⁽²⁾⁽³⁾	-4.5	A
	Pulsed Drain Current ⁽¹⁾ ⁽²⁾⁽³⁾	-4.5	A
I_G	Continuous Gate Clamp Current ⁽⁴⁾	-6	A
	Pulsed Gate Clamp Current ⁽⁴⁾	-6	A
P_D	Power Dissipation ⁽¹⁾	1.5	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

(1) May be limited by Max source current

(2) Based on Min Cu footprint

(3) Per MOSFET

(4) Total for device

 $R_{D1D2(on)}$ VS V_{GS}


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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV _{DSS}	Drain to Source Voltage	V _{GS} = 0V, I _D = -250μA	-20			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = -16V	-1			μA
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = ±8V	±100			nA
V _{GS(th)}	Gate to Source Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-0.7	-1.1	V
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = -1.8V, I _{DS} = -2A	50		70	mΩ
		V _{GS} = -2.5V, I _{DS} = -2A	39		50	mΩ
		V _{GS} = -4.5V, I _{DS} = -2A	32		40	mΩ
R _{DD(on)}	Drain to Drain On Resistance	V _{GS} = -1.8V, I _{DS} = -2A	80		110	mΩ
		V _{GS} = -2.5V, I _{DS} = -2A	61		75	mΩ
		V _{GS} = -4.5V, I _{DS} = -2A	46		55	mΩ
g _{fs}	Transconductance	V _{DS} = -10V, I _D = -2A	6.4			S
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V, V _{DS} = -10V, f = 1MHz	460		600	pF
C _{OSS}	Output Capacitance		220		290	pF
C _{RSS}	Reverse Transfer Capacitance		73		95	pF
R _G	Serialized Gate Resistance		1.6		3.2	Ω
Q _g	Gate Charge Total (-4.5V)	V _{DS} = -10V, I _D = -2A	4.5		5.9	nC
Q _{gd}	Gate Charge Gate to Drain		0.9			nC
Q _{gs}	Gate Charge Gate to Source		0.9			nC
Q _{g(th)}	Gate Charge at V _{th}		0.4			nC
Q _{OSS}	Output Charge		4.9			nC
t _{d(on)}	Turn On Delay Time	V _{DS} = -17V, V _{GS} = 0V	3.7			ns
t _r	Rise Time		4.1			ns
t _{d(off)}	Turn Off Delay Time		9.1			ns
t _f	Fall Time		1.6			ns
Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _D = -2A, V _{GS} = 0V	0.7		1	V
Q _{rr}	Reverse Recovery Charge	V _{DD} = -17V, I _F = -2A, di/dt = 300A/μs	11			nC
t _{rr}	Reverse Recovery Time		19			ns

THERMAL CHARACTERISTICS

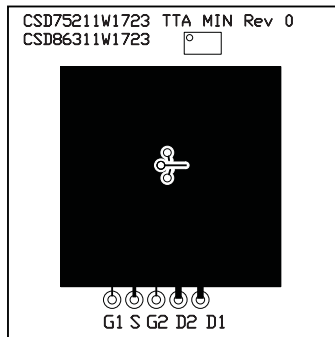
(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
R _{θJA}	Thermal Resistance Junction to Ambient (Minimum Cu area) ⁽¹⁾ ⁽²⁾			160	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient (1 in ² Cu area) ⁽²⁾ ⁽³⁾			69	°C/W

(1) Device mounted on FR4 material with minimum Cu mounting area.

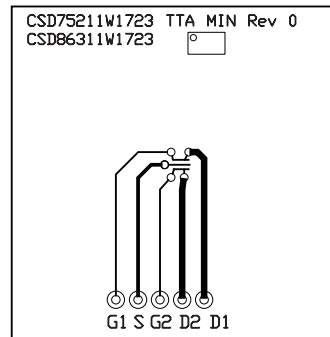
(2) Measured with both devices biased in a parallel condition.

(3) Device mounted on FR4 material with 1 in² of 2oz. Cu.



M0182-01

Max $R_{\theta JA} = 69^{\circ}\text{C/W}$
when mounted on
1inch² (6.45 cm²) of
2-oz. (0.071-mm thick)
Cu.

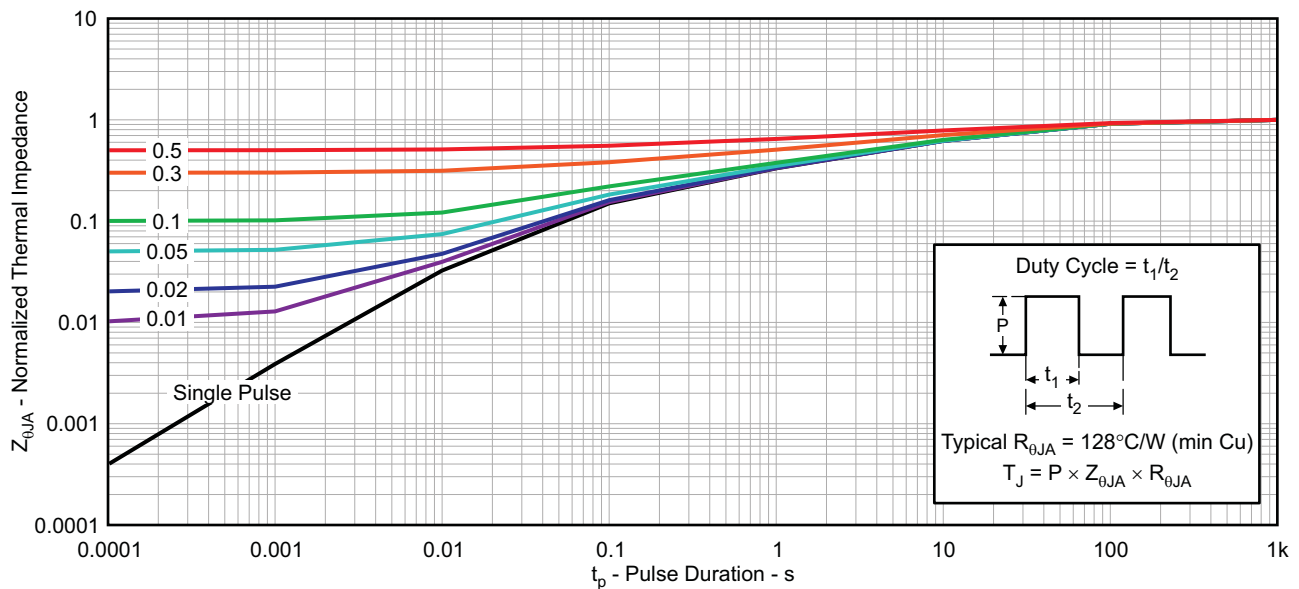


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Max $R_{\theta JA} = 160^{\circ}\text{C/W}$
when mounted on a
minimum pad area of
2-oz. (0.071-mm thick)
Cu.

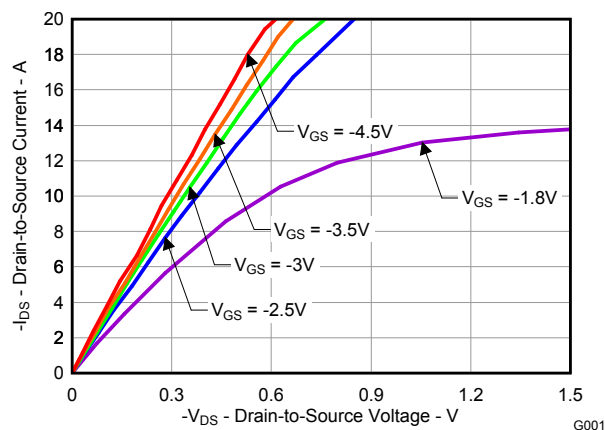
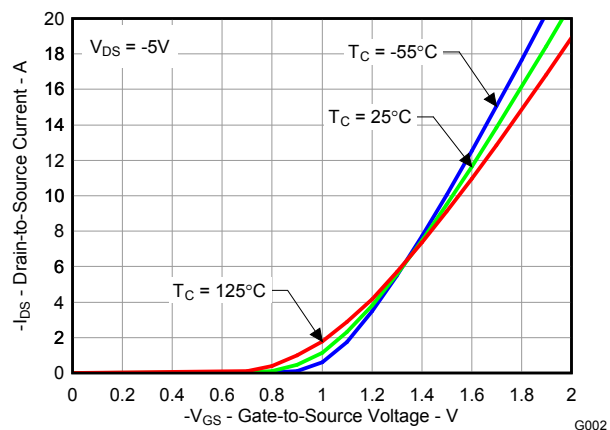
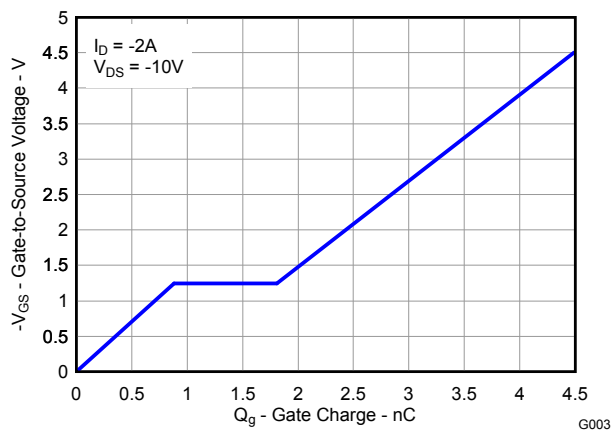
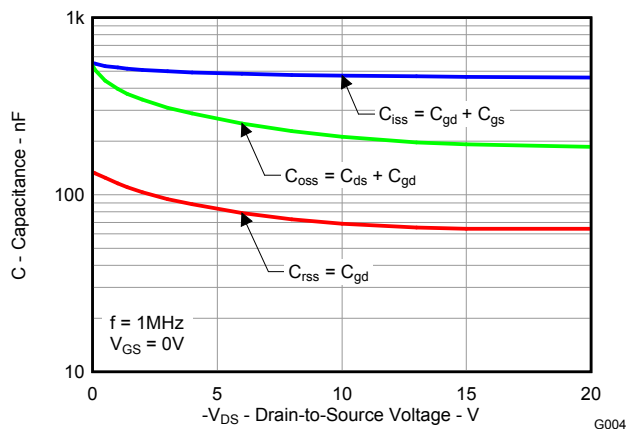
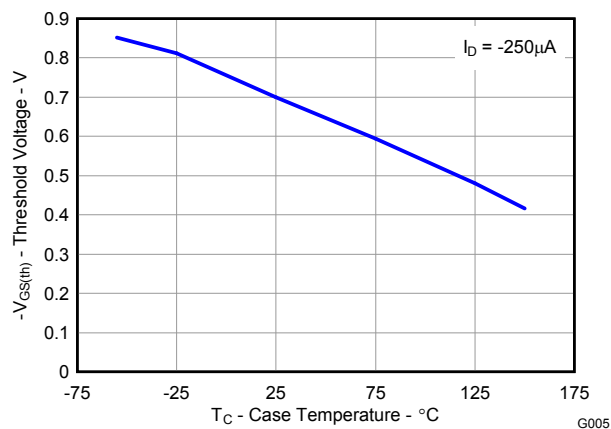
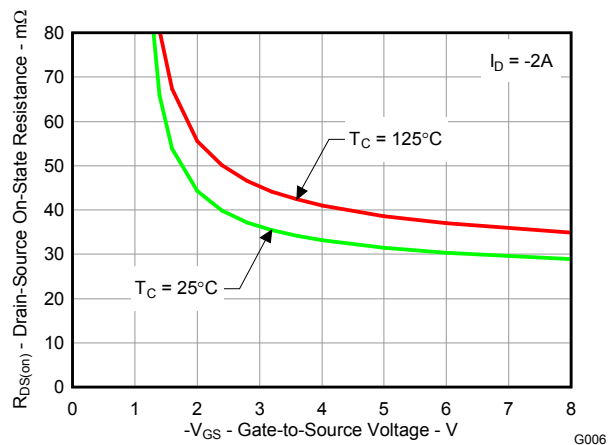
TYPICAL MOSFET CHARACTERISTICS

($T_A = 25^{\circ}\text{C}$ unless otherwise stated)



G012

Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)(T_A = 25°C unless otherwise stated)**Figure 2. Saturation Characteristics****Figure 3. Transfer Characteristics****Figure 4. Gate Charge****Figure 5. Capacitance****Figure 6. Threshold Voltage vs. Temperature****Figure 7. R_{DS(on)} vs. Gate-to-Source Voltage**

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

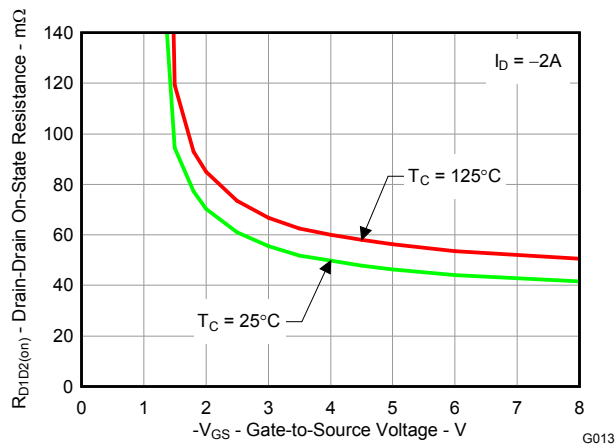


Figure 8. $R_{D1D2(on)}$ vs. Gate-to-Source Voltage

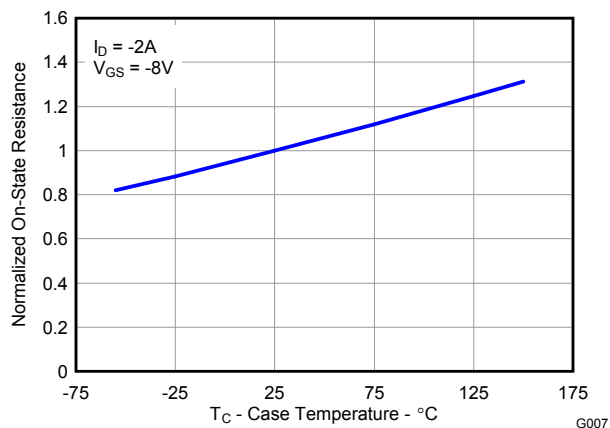


Figure 9. Normalized On-State Resistance vs. Temperature

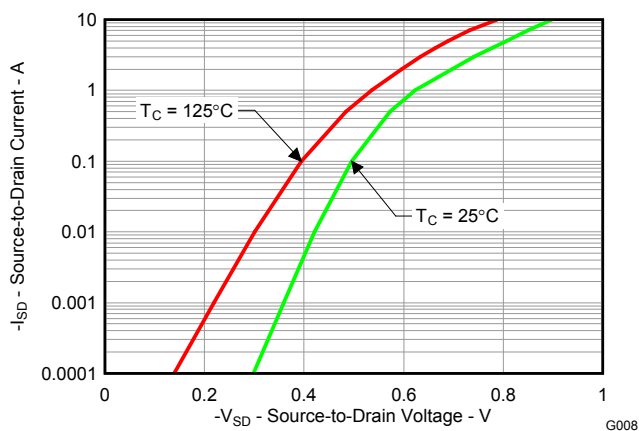


Figure 10. Typical Diode Forward Voltage

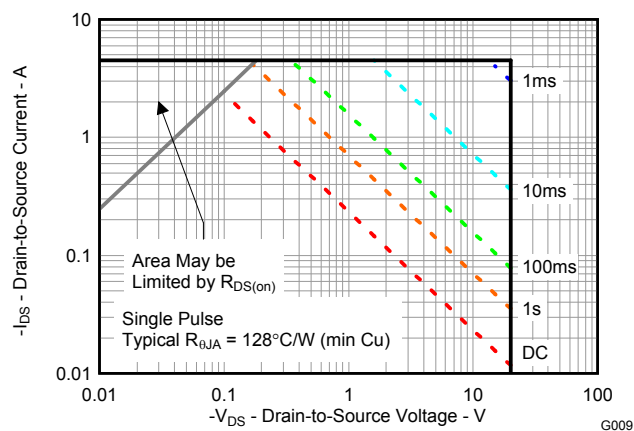


Figure 11. Maximum Safe Operating Area

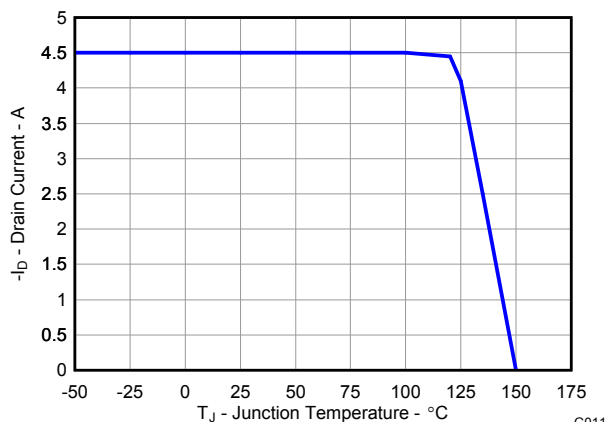
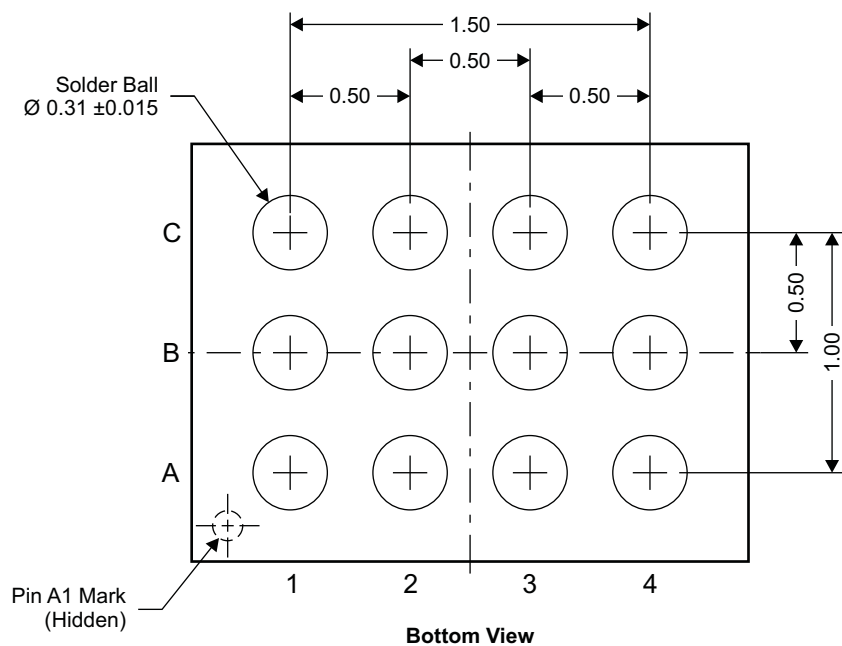
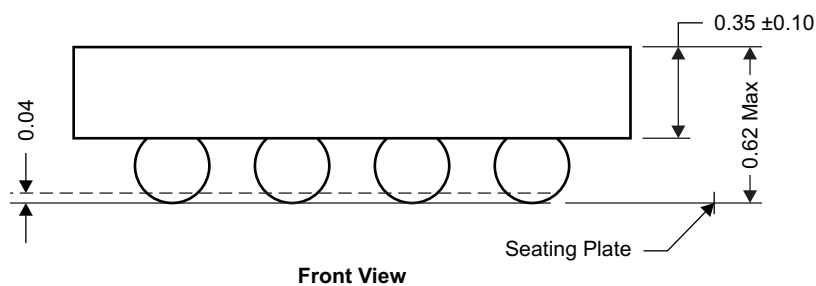
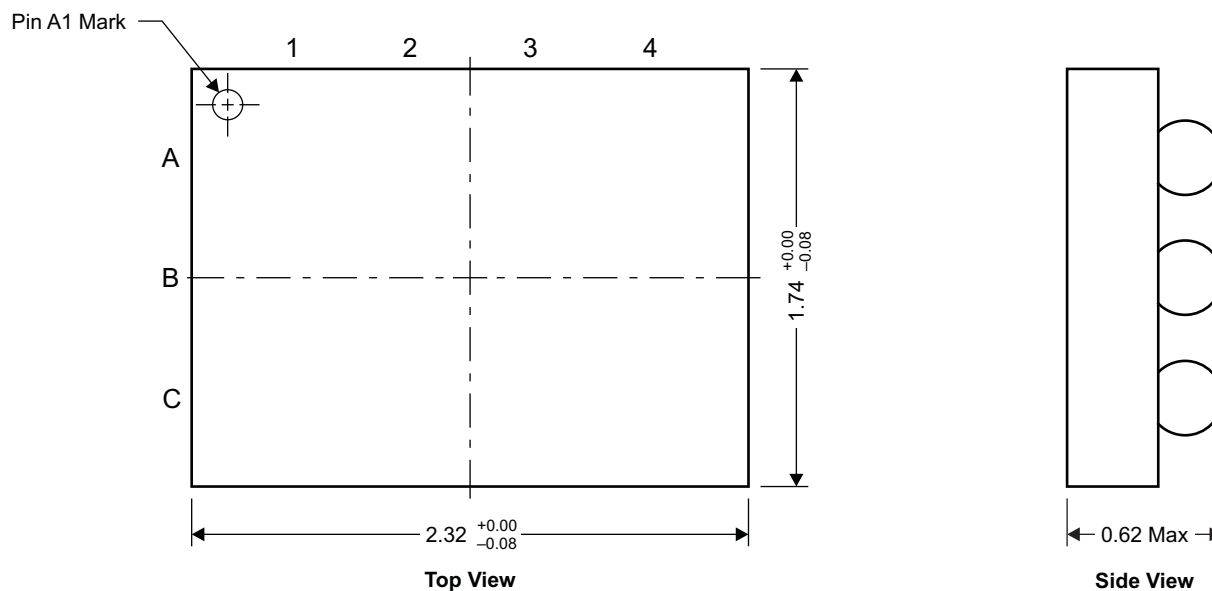


Figure 12. Maximum Drain Current vs. Temperature

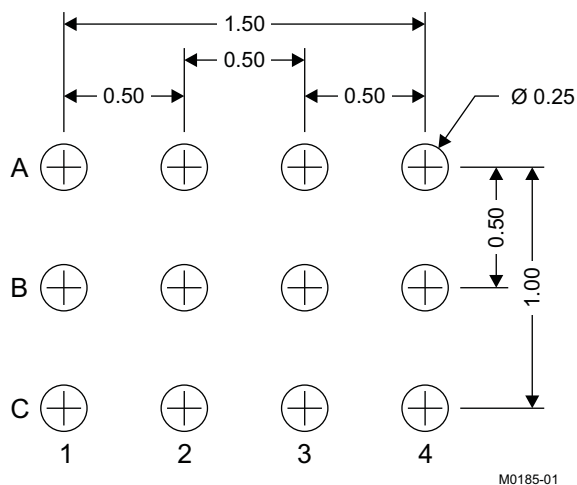
MECHANICAL DATA**CSD75211W1723 Package Dimensions**

Pinout	
Position	Designation
A2, A3, A4	Drain 1
C2, C3, C4	Drain 2
A1	Gate 1
C1	Gate 2
B1, B2, B3, B4	Source

NOTE: All dimensions are in mm (unless otherwise specified)

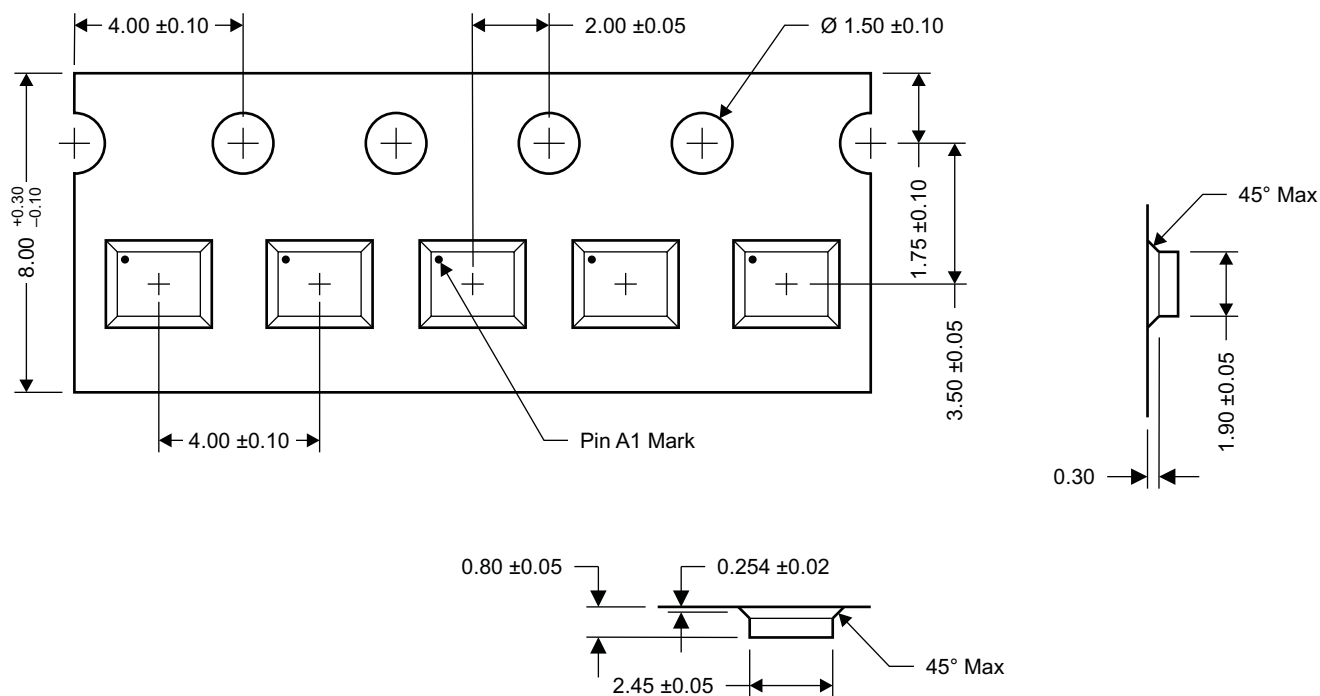
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Land Pattern Recommendation



NOTE: All dimensions are in mm (unless otherwise specified)

Tape and Reel Information



NOTE: All dimensions are in mm (unless otherwise specified)

REVISION HISTORY

Changes from Original (May 2010) to Revision A

Page

- Changed V_{GS} in the Abs Max Ratings table From: +8 To: ± 8 [1](#)

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